

NJ01 Process

Silicon Junction Field-Effect Transistor

- Low-Current
- Low Gate Leakage Current
- High Input Impedance

Absolute maximum ratings at TA = 25 °C

Gate Current, Ig	10 mA
Operating Junction Temperature, Tj	+150°C
Storage Temperature, Ts	– 65°C to +175°C

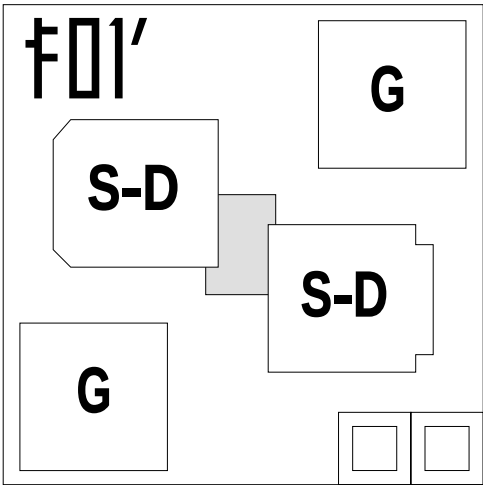
Devices in this Databook based on the NJ01 Process.

Datasheet

2N4117, 2N4117A
2N4118, 2N4118A
2N4119, 2N4119A
IFN421, IFN422
IFN423, IFN424
IFN425, IFN426

Datasheet

DPAD1, DPAD2
DPAD5, DPAD10
PAD1, PAD2
PAD5
VCR7N



Die Size = 0.016" X 0.016"
All Bond Pads = 0.004" Sq.
Substrate is also Gate.

www.DataSheet4U.com

At 25°C free air temperature:		NJ01 Process					
		Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	V _{(BR)GSS}	– 40	– 50		V	I _G = – 1 µA, V _{DS} = 0V	
Gate Reverse Current	I _{GSS}		– 0.5	– 10	pA	V _{GS} = – 20V, V _{DS} = 0V	
Gate Source Cutoff Voltage	V _{GS(OFF)}	– 0.5		– 6	V	V _{DS} = 10V, I _D = 1 µA	
Drain Saturation Current (Pulsed)	I _{DSS}	0.03		0.6	mA	V _{DS} = 10V, V _{GS} = 0V	
Dynamic Electrical Characteristics							
Common Source Forward Transconductance	g _{fs}		175		µS	V _{DS} = 10V, V _{GS} = 0V	f = 1 kHz
Common Source Input Capacitance	C _{iss}		2		pF	V _{DS} = 10V, V _{GS} = 0V	f = 1 MHz
Common Source Reverse Transfer Capacitance	C _{rss}		0.9		pF	V _{DS} = 10V, V _{GS} = 0V	f = 1 MHz

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